

2SK302500L Datasheet



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DiGi Electronics Part Number 2SK302500L-DG

Manufacturer Panasonic Electronic Components

Manufacturer Product Number 25K302500L

Description MOSFET N-CH 60V 30A U-DL

Detailed Description N-Channel 60 V 30A (Tc) 1W (Ta), 25W (Tc) Surface

Mount U-DL



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
25K302500L	Panasonic Electronic Components
Series:	Product Status:
	Obsolete
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
60 V	30A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
4V, 10V	40mOhm @ 15A, 10V
Vgs(th) (Max) @ Id:	Vgs (Max):
2.5V @ 1mA	±20V
Input Capacitance (Ciss) (Max) @ Vds:	FET Feature:
1200 pF @ 10 V	
Power Dissipation (Max):	Operating Temperature:
1W (Ta), 25W (Tc)	150°C (TJ)
Mounting Type:	Supplier Device Package:
Surface Mount	U-DL
Package / Case:	
TO-252-4. DPAK (3 Leads + Tab)	

Environmental & Export classification

Moisture Sensitivity Level (MSL):	ECCN:
1 (Unlimited)	EAR99
HTSUS:	
8541.29.0095	

2SK3025

Silicon N-channel power MOS FET

■ Features

- Avalanche energy capability guaranteed
- High-speed switching
- Low ON resistance Ron
- No secondary breakdown
- Low-voltage drive
- High electrostatic energy capability

■ Applications

- Non-contact relay
- Solenoid drive
- Motor drive
- Control equipment
- Switching mode regulator

■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit
Drain-source surrender voltage	V _{DSS}	60	V
Gate-source surrender voltage	V _{GSS}	±20	V
Drain current	I_{D}	±30	A
Peak drain current	I_{DP}	±90	A
Avalanche energy capability *	EAS	45	mJ
Power dissipation	P_{D}	25	W
$T_a = 25^{\circ}C$		1	
Channel temperature	T_{ch}	150	S °C
Storage temperature	T _{stg}	-55 to +150	°C
			2.0.

Note) *: L = 0.1 mH, $I_L = 30 \text{ A}$, 1 pulse

■ Electrical Characteristics T_C = 25°C ± 3°C

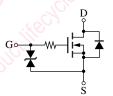
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source surrender voltage	V _{DSS}	$I_D = 1 \text{ mA}, V_{GS} = 0$	60			V
Drain-source cutoff current	I_{DSS}	$V_{DS} = 50 \text{ V}, V_{GS} = 0$	16		10	μΑ
Gate-source cutoff current	I_{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$			±10	μΑ
Gate threshold voltage	V _{th}	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$	1.0		2.5	V
Forward transfer admittance	Y _{fs}	$V_{DS} = 10 \text{ V}, I_D = 15 \text{ A}$	10	18		S
Drain-source ON resistance	R _{DS(on)1}	$V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$		25	40	mΩ
	R _{DS(on)2}	$V_{GS} = 4 \text{ V}, I_D = 15 \text{ A}$		35	55	
Diode forward voltage	V _{DSF}	$I_{DR} = 15 \text{ A}, V_{GS} = 0$			-1.3	V
Short-circuit forward transfer capacitance (Common source)	C _{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		1200		pF
Short-circuit output capacitance (Common source)	C _{oss}	*		400		pF
Reverse transfer capacitance (Common source)	C _{rss}			200		pF
Turn-on delay time	t _{d(on)}	$V_{DD} = 30 \text{ V}, I_D = 15 \text{ A}, R_L = 2 \Omega$		10		ns
Rise time	t _r	$V_{GS} = 10 \text{ V}$		20		ns
Fall time	t _f			140		ns
Turn-off delay time	t _{d(off)}			350		ns
Thermal resistance (ch-c)	R _{th(ch-c)}				5.0	°C/W
Thermal resistance (ch-a)	R _{th(ch-a)}				125	°C/W

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

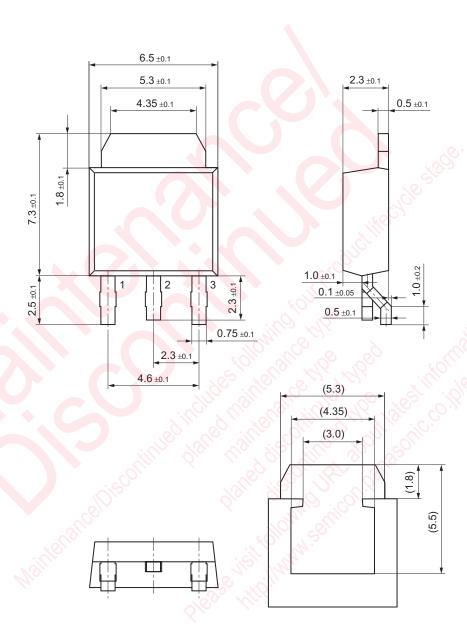
■ Package

- Code
- U-DL
 Pin Name
 - 1: Gate
 - 2: Drain
 - 3: Source
- Marking Symbol: K3025

Internal Connection



U-DL Unit: mm



2 SJG00011CED

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